

# BRCS3407MC

Rev.F May.-2025

## 描述 / Descriptions

SOT23-3 塑封封装 P 道 MOS 场效应管。

P- CHANNEL MOSFET in a SOT23-3 Plastic Package.

## 特征 / Features

$V_{DS} (V) = -30V$

$I_D = -4.1 A$

$R_{DS(ON)} < 60m\Omega (V_{GS} = -10V)$

$R_{DS(ON)} < 85m\Omega (V_{GS} = -4.5V)$

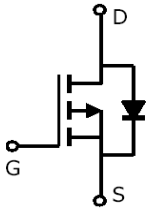
无卤产品。HF Product.

## 用途 / Applications

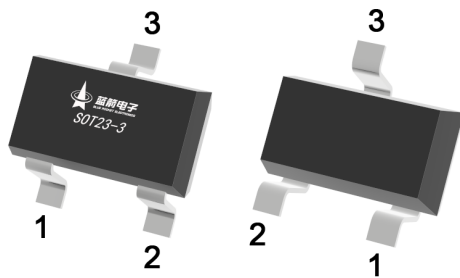
适用于作负载开关或脉宽调制应用。

This device is suitable for use as a load switch or in PWM applications.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN1 : G

PIN 2 : S

PIN 3 : D

## 印章代码 / Marking

Marking

A7H

**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V <sub>DS</sub>	-30	V
Drain Current – Continuous	I <sub>D</sub>	-4.1	A
Drain Current- Continuous	I <sub>D</sub> (T <sub>a</sub> =70°C)	-3.5	A
Pulsed Drain Current	I <sub>DM</sub>	-20	A
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Total Power Dissipation	P <sub>D</sub>	1.4	W
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	125	°C/W
Thermal Resistance-Junction to Lead	R <sub>θJL</sub>	80	

**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain–Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V V <sub>GS</sub> =0V			-1	μA
		V <sub>DS</sub> =-24V V <sub>GS</sub> =0V T <sub>J</sub> =55°C			-5	μA
Gate–Body Leakage.	I <sub>GSS</sub>	V <sub>GS</sub> =±20V V <sub>DS</sub> =0V			±0.1	μA
On–State Drain Current	I <sub>D(on)</sub>	V <sub>GS</sub> =-4.5V V <sub>DS</sub> =-5V	-10			A
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =-250μA	-1	-1.5	-3	V
Static Drain–Source On–Resistance	R <sub>DS(on)1</sub>	V <sub>GS</sub> =-10V I <sub>D</sub> =-4.1A		54	60	mΩ
	R <sub>DS(on)2</sub>	V <sub>GS</sub> =-10V I <sub>D</sub> =-4.1A T <sub>J</sub> =125°C		57	73	
	R <sub>DS(on)3</sub>	V <sub>GS</sub> =-4.5V I <sub>D</sub> =-3A		77	85	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V I <sub>D</sub> =-4A		4.9		S
Drain–Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V I <sub>S</sub> =-1A		-0.77	-1	V
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V V <sub>GS</sub> =0V f=1MHz		830		pF
Output Capacitance	C <sub>oss</sub>			410		
Reverse Transfer Capacitance	C <sub>rss</sub>			200		

## 电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Total Gate Charge	$Q_g(10V)$	$V_{GS}=-10V, V_{DS}=-15V,$ $I_D=-4.1A$		8.5		nC
Total Gate Charge	$Q_g(4.5V)$			4.5		
Gate Source Charge	$Q_{gs}$			1.5		
Gate Drain Charge	$Q_{gd}$			2.0		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=-10V R_L=3.6\Omega$ $V_{DS}=-15V R_{GEN}=3\Omega$		7.3		ns
Turn-On Rise Time	$t_r$			4.3		
Turn-Off Delay Time	$t_{d(off)}$			25.2		
Turn-Off Fall Time	$t_f$			12.5		
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F=-4.1A, dI/dt=100A/\mu s$		10		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F=-4.1A, dI/dt=100A/\mu s$		5.2		nC

电参数曲线图 / Electrical Characteristic Curve

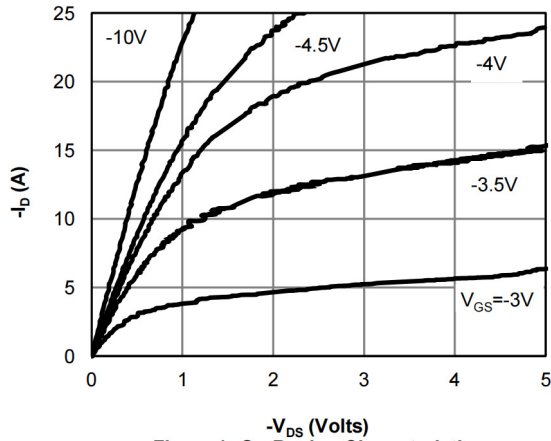


Figure 1: On-Region Characteristics

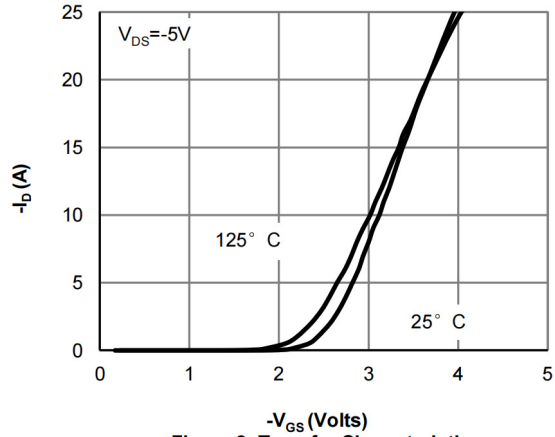


Figure 2: Transfer Characteristics

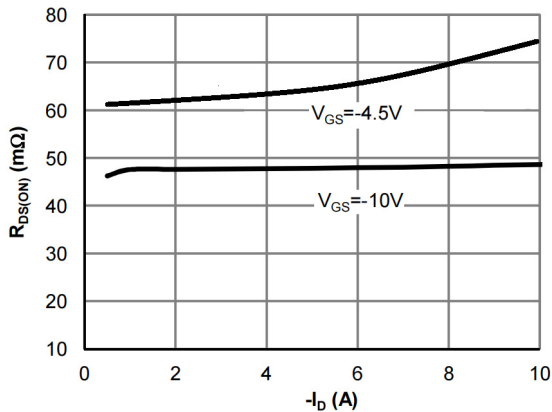


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

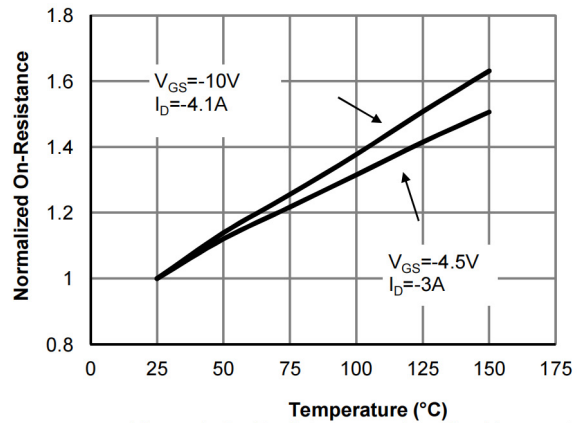


Figure 4: On-Resistance vs. Junction Temperature

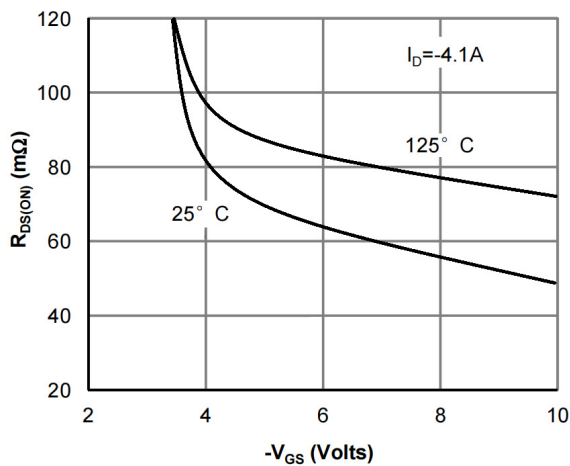


Figure 5: On-Resistance vs. Gate-Source Voltage

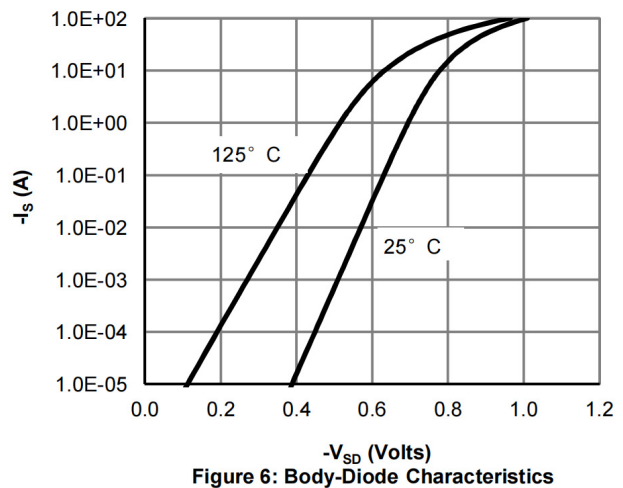
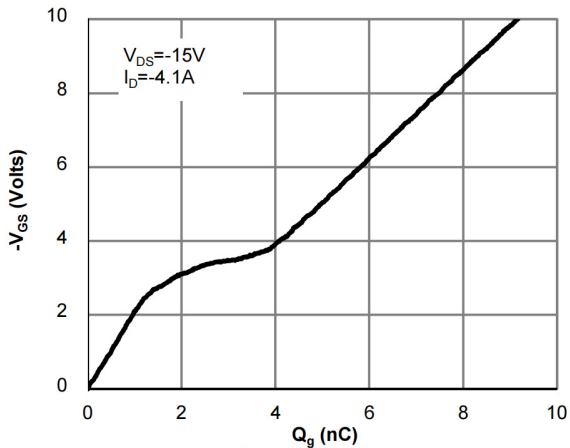
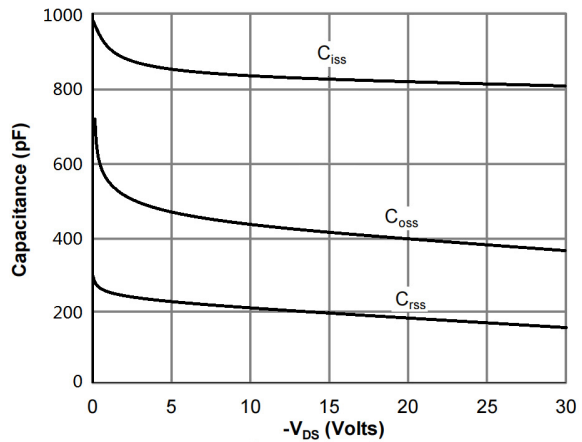


Figure 6: Body-Diode Characteristics

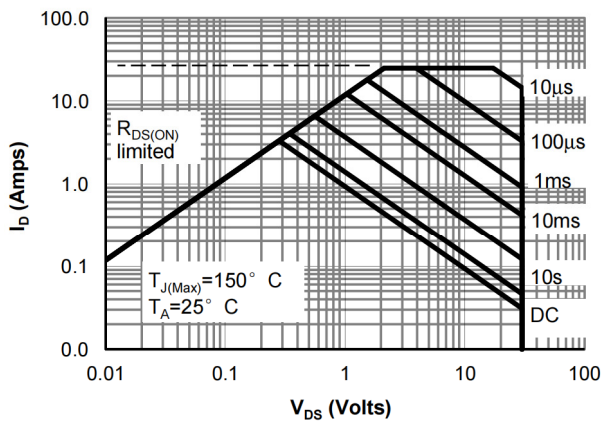
**电参数曲线图 / Electrical Characteristic Curve**



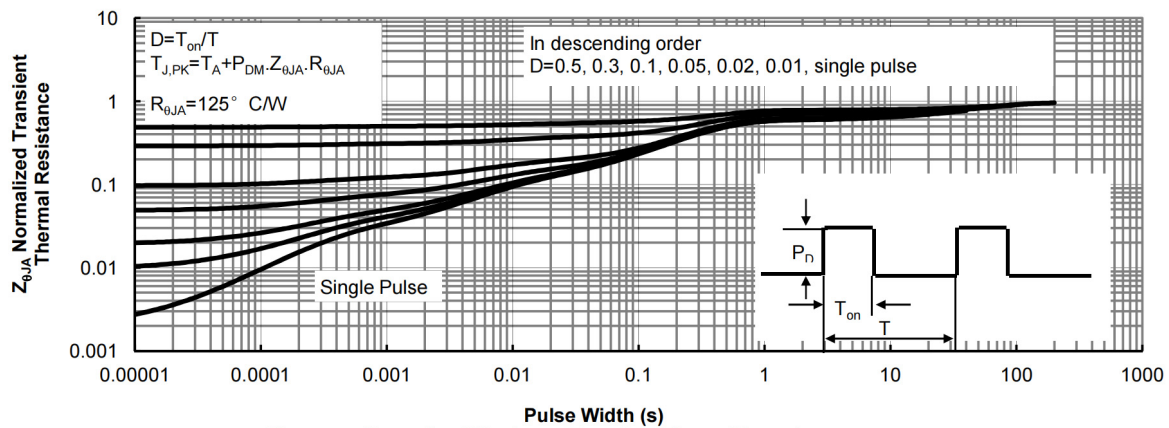
**Figure 7: Gate-Charge Characteristics**



**Figure 8: Capacitance Characteristics**

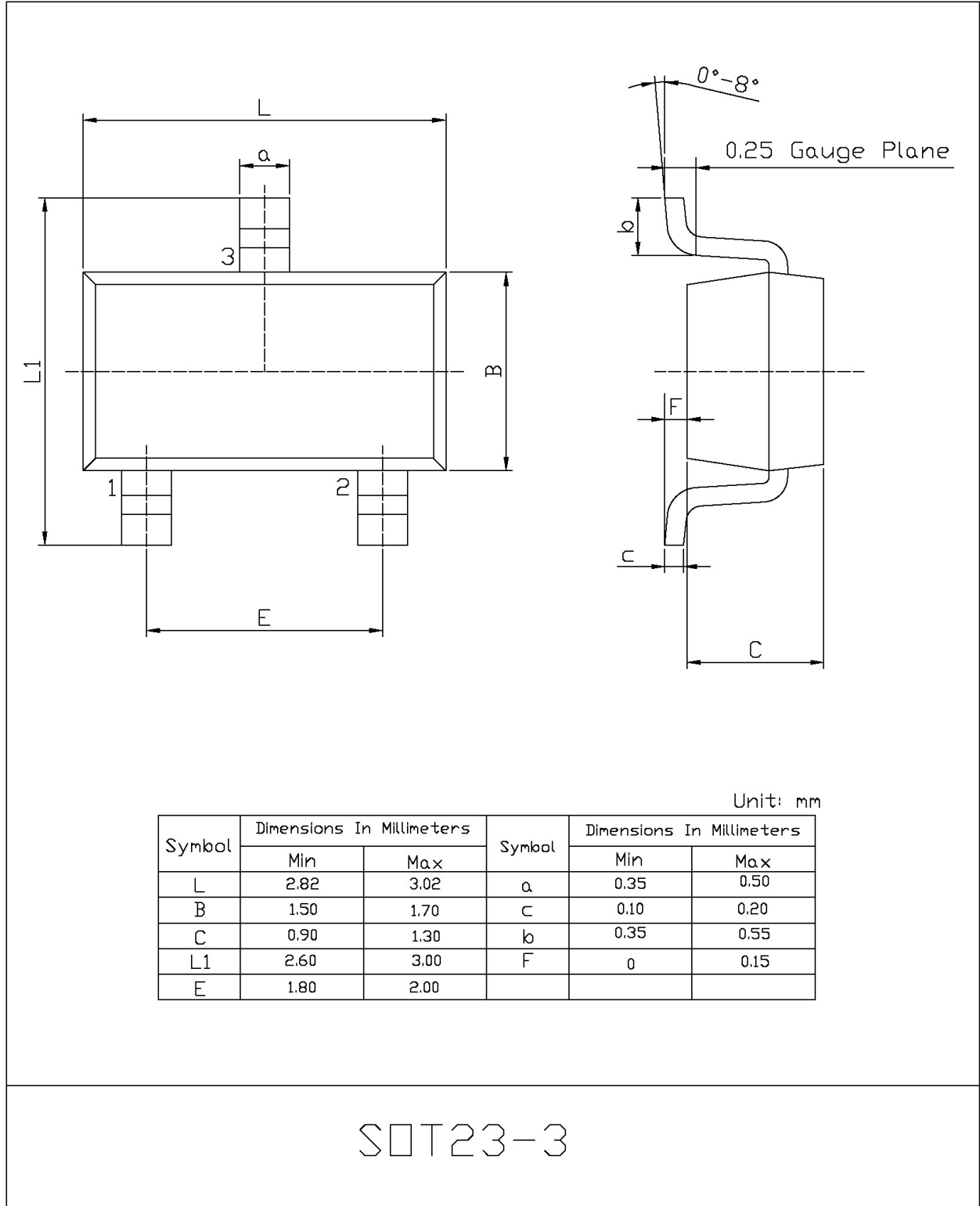


**Figure 9: Maximum Forward Biased Safe Operating Area**



**Figure 10: Normalized Maximum Transient Thermal Impedance**

**外形尺寸图 / Package Dimensions**

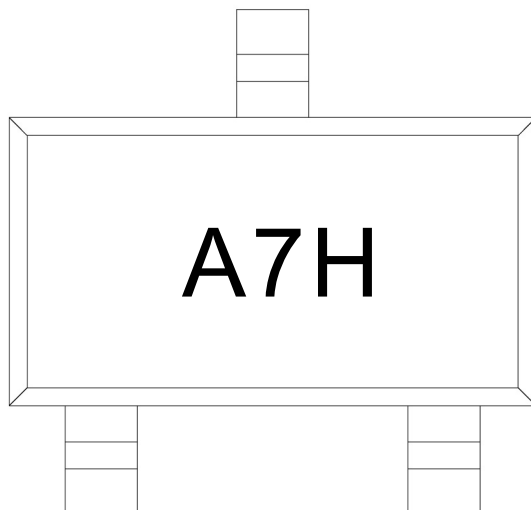


Unit: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.82	3.02	a	0.35	0.50
B	1.50	1.70	c	0.10	0.20
C	0.90	1.30	b	0.35	0.55
L1	2.60	3.00	F	0	0.15
E	1.80	2.00			

SOT23-3

**印章说明 / Marking Instructions**



说明：

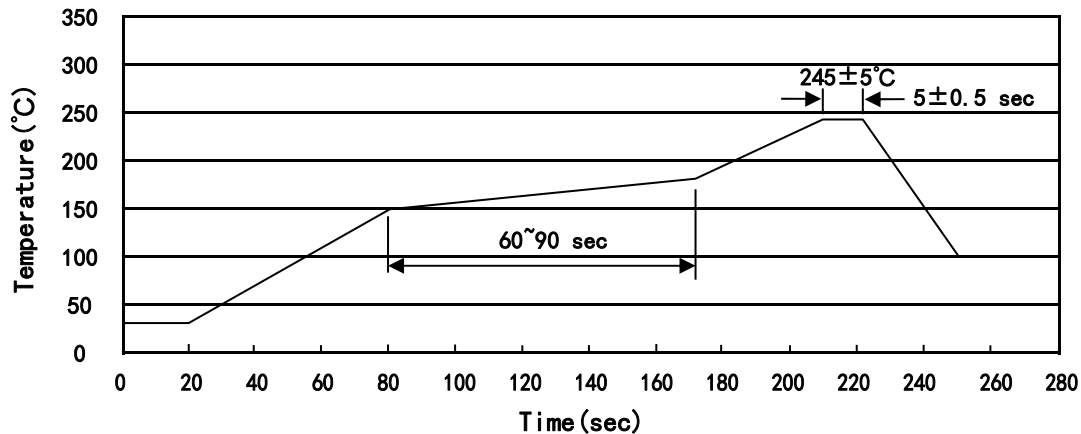
A7： 为型号代码

H： 为公司代码

Note:

A7: Product Type Code

H: Company Code

**回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)**


说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT23-3	3,000	10	30,000	4	120,000	7" ×8	210×205×205	445×435×230

**使用说明 / Notices**